2SB857, 2SB858

Silicon PNP Triple Diffused

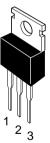
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Application

Low frequency power amplifier complementary pair with 2SD1133 and 2SD1134

Outline

TO-220AB



- 1. Base
- 2. Collector (Flange)
- 3. Emitter

Absolute Maximum Ratings $(Ta = 25^{\circ}C)$

		Ratings		
Item	Symbol	2SB857	2SB858	Unit
Collector to base voltage	V _{CBO}	-7 0	-7 0	V
Collector to emitter voltage	V_{CEO}	- 50	-60	V
Emitter to base voltage	V_{EBO}	- 5	- 5	V
Collector current	I _c	-4	-4	A
Collector peak current	I _{C(peak)}	-8	-8	Α
Collector power dissipation	Pc*1	40	40	W
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-45 to +150	-45 to +150	°C

Note: 1. Value at $T_c = 25^{\circ}C$



2SB857, 2SB858

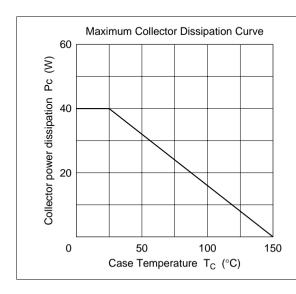
Electrical Characteristics ($Ta = 25^{\circ}C$)

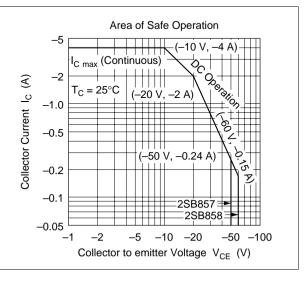
		2SB8	57		2SB858				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-70	_	_	-70	_	_	V	$I_{c} = -10 \mu\text{A}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{\text{(BR)CEO}}$	- 50	_	_	-60	_	_	V	$I_{\rm C} = -50$ mA, $R_{\rm BE} = \infty$
Emitter to base breakdown voltage	$V_{\text{(BR)EBO}}$	- 5	_	_	- 5	_	_	V	$I_{E} = -10 \mu A, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	-1	_	_	-1	μΑ	$V_{CB} = -50 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE1} *1	60	_	320	60	_	320		$V_{CE} = I_{C} = -1 A^{*2}$
	h _{FE2}	35	_	_	35	_	_		$-4 \text{ V} \qquad \overline{I_{\text{C}} = -0.1 \text{ A}^{*2}}$
Collector to emitter saturation voltage	V _{CE(sat)}	_	_	-1	_	_	-1	V	$I_{\rm C} = -2 \text{ A}, I_{\rm B} = -0.2 \text{ A}^{*2}$
Base to emitter voltage	V_{BE}	_	_	-1	_	_	-1	V	$V_{CE} = -4 \text{ V}, I_{C} = -1 \text{ A}^{*2}$
Gain bandwidth product	f _T	_	15	_	_	15	_	MHz	$V_{CE} = -4 \text{ V},$ $I_{C} = -0.5 \text{ A}^{*2}$

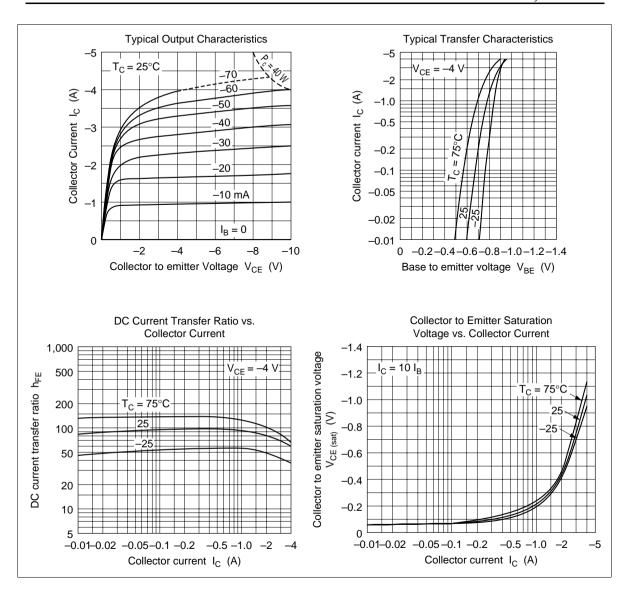
Notes: 1. The 2SB857 and 2SB858 are grouped by h_{FE1} as follows.

2. Pulse test

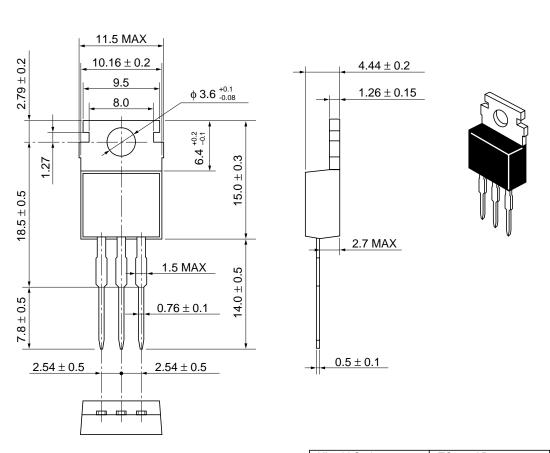
В	С	D
60 to 120	100 to 200	160 to 320







Unit: mm



Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

Cautions

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom

Tel: <44> (1628) 585000 Fax: <44> (1628) 778322 Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218

Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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